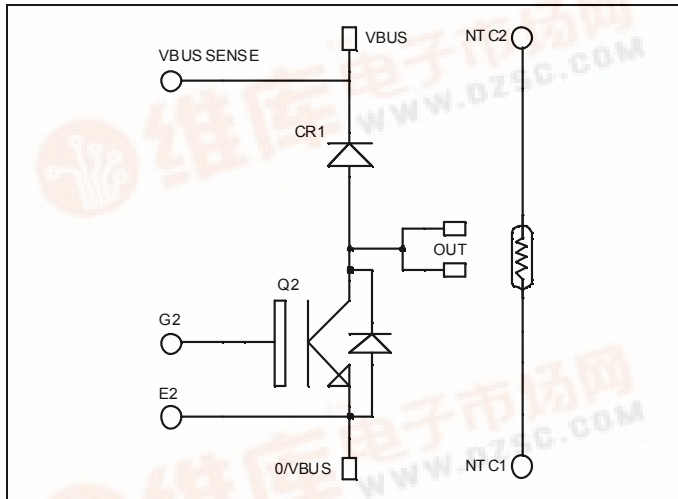




APTGT100DA170TG

Boost chopper Trench + Field Stop IGBT® Power Module

$V_{CES} = 1700V$
 $I_C = 100A @ T_c = 80^\circ C$

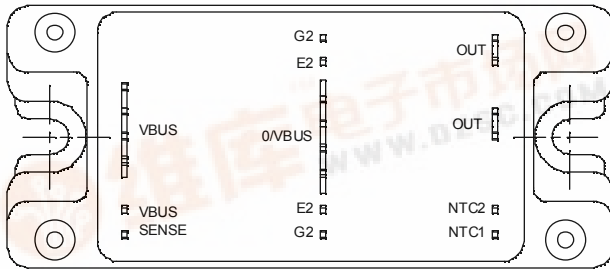


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$ 150 $T_c = 80^\circ C$ 100	A
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$ 200	
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$ 560	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$ 200A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 100A$	$T_j = 25^\circ\text{C}$	2.0	2.4	V
			$T_j = 125^\circ\text{C}$	2.4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V$		9		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.36		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.3		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 100A$ $R_G = 4.7 \Omega$		370		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 100A$ $R_G = 4.7 \Omega$		400		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			800		
T_f	Fall Time			300		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 100A$ $R_G = 4.7 \Omega$	$T_j = 125^\circ\text{C}$	32		mJ
E_{off}	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$	31		

Chopper diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700V$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$	100		A
V_F	Diode Forward Voltage	$I_F = 100A$	$T_j = 25^\circ\text{C}$	1.8	2.2	V
			$T_j = 125^\circ\text{C}$	1.9		
t_{rr}	Reverse Recovery Time	$I_F = 100A$ $V_R = 900V$ $di/dt = 1000A/\mu s$	$T_j = 25^\circ\text{C}$	385		ns
			$T_j = 125^\circ\text{C}$	490		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	25		μC
			$T_j = 125^\circ\text{C}$	42		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	11		mJ
			$T_j = 125^\circ\text{C}$	21		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

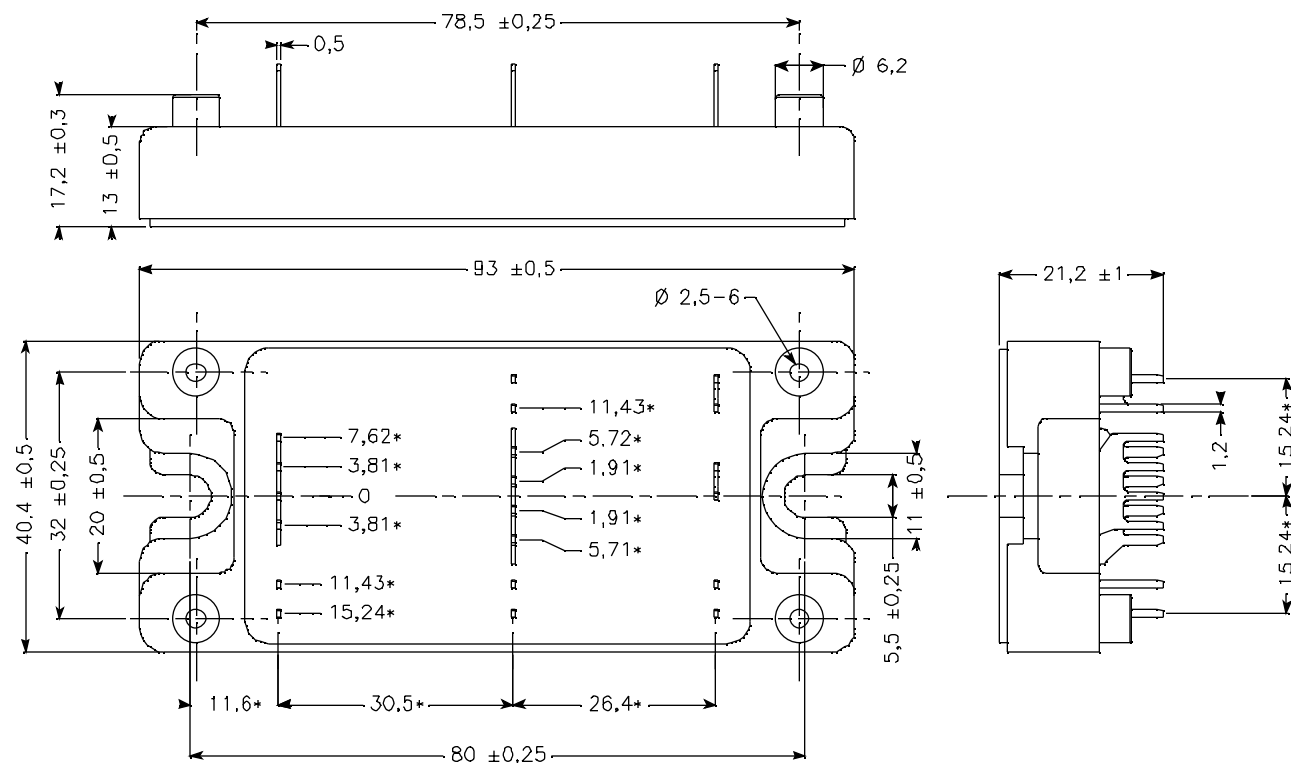
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance			IGBT		0.22	°C/W
				Diode		0.39	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			3500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

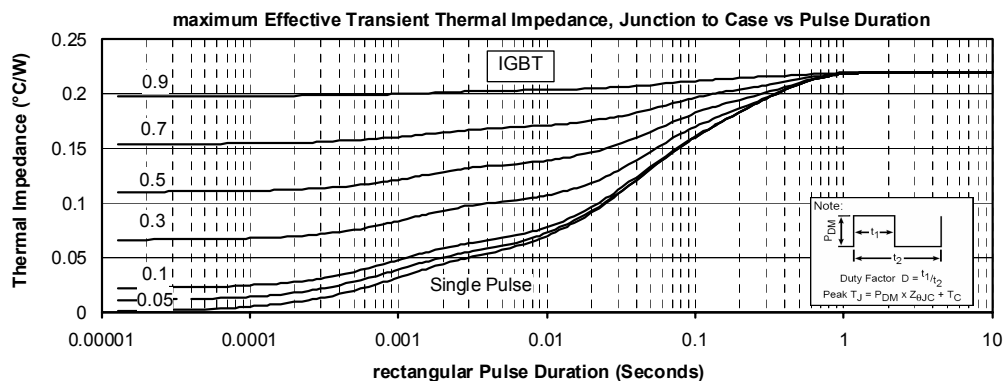
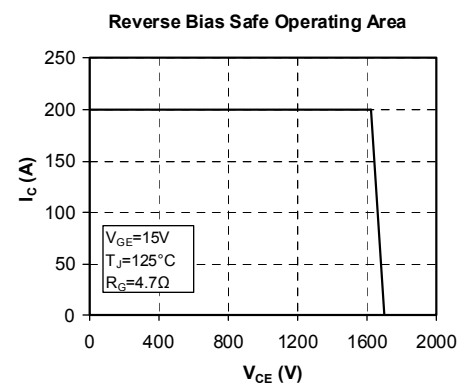
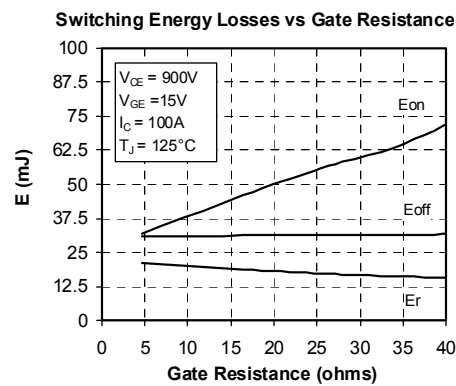
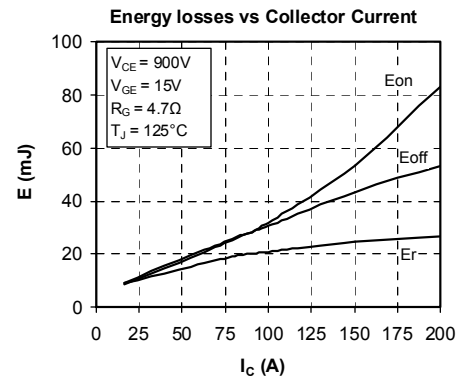
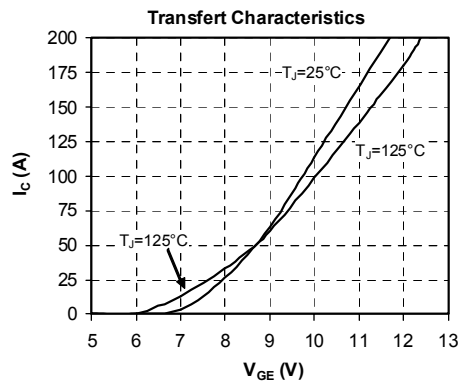
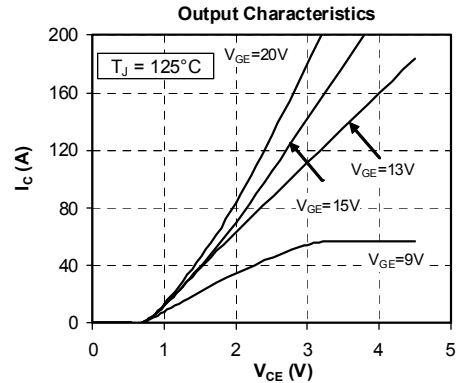
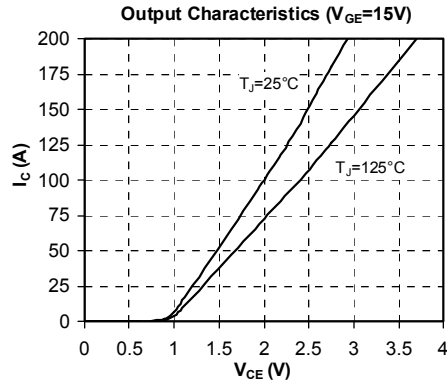
SP4 Package outline (dimensions in mm)

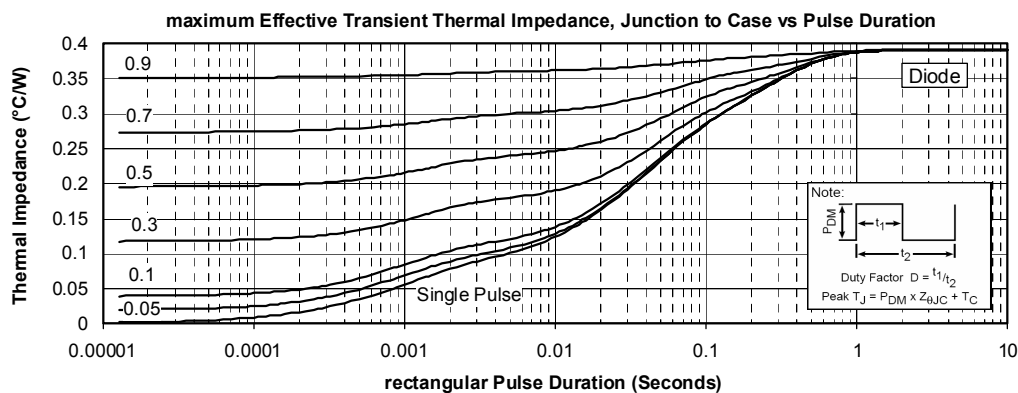
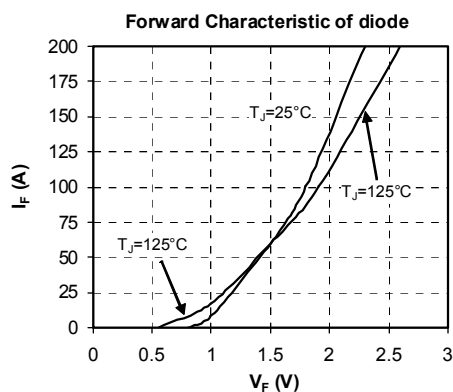
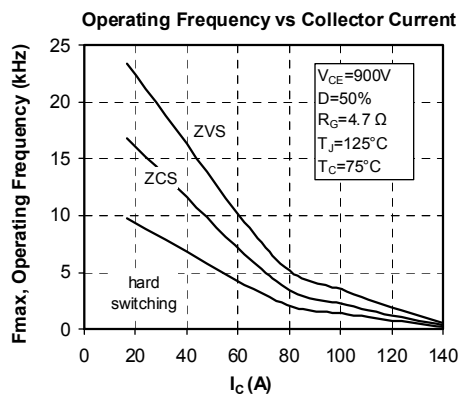


ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS: $\pm 0,1$

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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